

# N-channel 25 V 2.8 m $\Omega$ logic level MOSFET in LFPAK33 using NextPower Technology

Rev. 3 — 15 June 2012

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

### 1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions   | Min          | Тур  | Max  | Unit |
|-------------------|----------------------------------|--|--------------|------|------|------|
| $V_{DS}$          | drain-source voltage             | $T_j = 25^{\circ}C$  | -            | -    | 25   | V    |
| I <sub>D</sub>    | drain current                    | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>   | <u>[1]</u> - | -    | 70   | Α    |
| P <sub>tot</sub>  | total power dissipation          | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   | -            | -    | 88   | W    |
| T <sub>j</sub>    | junction temperature             |  | -55          | -    | 175  | °C   |
| Static charact    | teristics                        |  |              |      |      |      |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$<br>see <u>Figure 10</u> | -            | 3.25 | 3.75 | mΩ   |
|                   |                                  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 10            | -            | 2.45 | 2.8  | mΩ   |
| Dynamic char      | racteristics                     |  |              |      |      |      |
| $Q_{GD}$          | gate-drain charge                | $V_{GS}$ = 4.5 V; $I_D$ = 25 A; $V_{DS}$ = 12.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u>   | -            | 3.9  | -    | nC   |
| $Q_{G(tot)}$      | total gate charge                | $V_{GS}$ = 4.5 V; $I_D$ = 25 A; $V_{DS}$ = 12.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u>   | -            | 16.3 | -    | nC   |

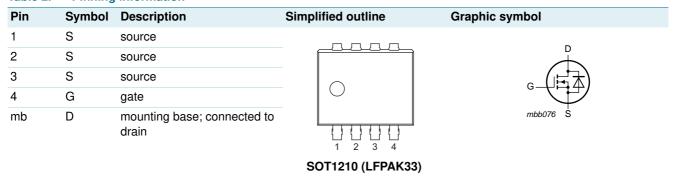
<sup>[1]</sup> Continuous current is limited by package.



N-channel 25 V 2.8 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

### 2. Pinning information

Table 2. Pinning information



### 3. Ordering information

Table 3. Ordering information

| Type number   | Package |   |         |  |
|---------------|---------|---|---------|--|
|               | Name    | Description   | Version |  |
| PSMN2R8-25MLC | LFPAK33 | Plastic single ended surface mounted package (LFPAK33); 4 leads | SOT1210 |  |

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                    | Conditions   | Min          | Max | Unit |
|----------------------|--|--|--------------|-----|------|
| $V_{DS}$             | drain-source voltage                         | $T_j = 25^{\circ}C$  | -            | 25  | V    |
| $V_{GS}$             | gate-source voltage                          |  | -20          | 20  | V    |
| $I_D$                | drain current                                | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>   | <u>[1]</u> - | 70  | Α    |
|                      |  | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>  | [1] -        | 70  | Α    |
| I <sub>DM</sub>      | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 4   | -            | 536 | Α    |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   | -            | 88  | W    |
| T <sub>stg</sub>     | storage temperature                          |  | -55          | 175 | °C   |
| Tj                   | junction temperature                         |  | -55          | 175 | °C   |
| $T_{sld(M)}$         | peak soldering temperature                   |  | -            | 260 | °C   |
| $V_{ESD}$            | electrostatic discharge voltage              | MM (JEDEC JESD22-A115)   | 350          | -   | V    |
| Source-drain         | diode  |  |              |     |      |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C  | <u>[1]</u> _ | 70  | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$   | -            | 536 | Α    |
| Avalanche ru         | iggedness                                    |  |              |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 70 A; $V_{sup} \le$ 25 V; $R_{GS}$ = 50 $\Omega$ ; unclamped; see Figure 3 | -            | 77  | mJ   |

[1] Continuous current is limited by package.

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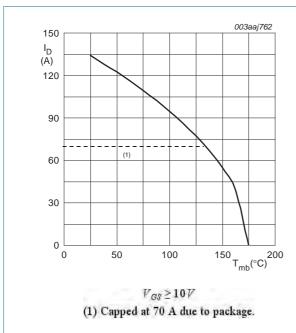


Fig 1. Continuous drain current as a function of mounting base temperature

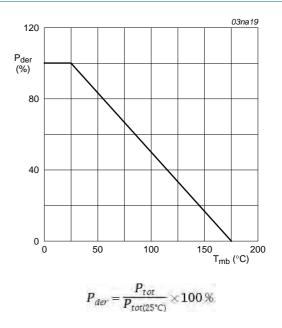


Fig 2. Normalized total power dissipation as a function of mounting base temperature

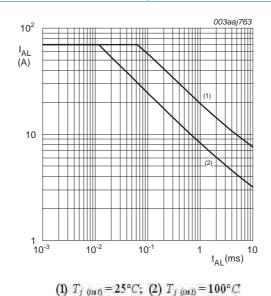
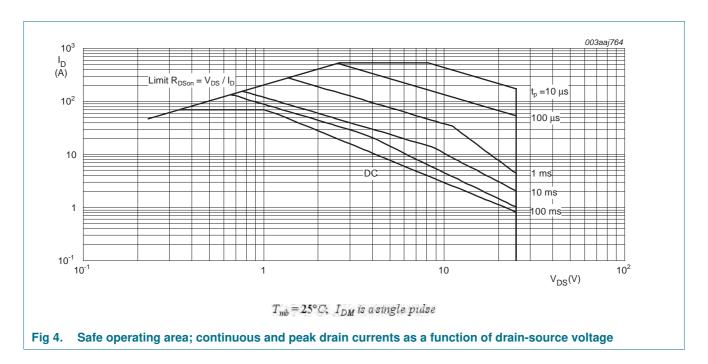


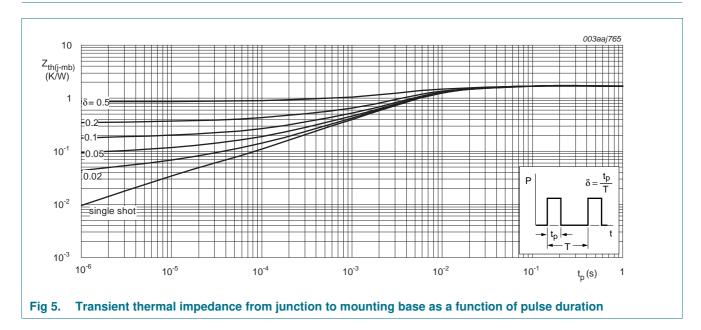
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



### 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol                | Parameter   | Conditions          | Min | Тур  | Max | Unit |
|-----------------------|---|---------------------|-----|------|-----|------|
| $R_{th(j\text{-}mb)}$ | thermal resistance from junction to mounting base | see <u>Figure 5</u> | -   | 1.49 | 1.7 | K/W  |



### 6. Characteristics

Table 6. Characteristics

| Symbol                       | Parameter  | Conditions  | Min  | Тур  | Max  | Unit |
|------------------------------|--|---|------|------|------|------|
| Static charac                | cteristics   |   |      |      |      |      |
| V <sub>(BR)DSS</sub>         | drain-source   | $I_D = 250 \mu A; V_{GS} = 0 V; T_i = 25 °C$  | 25   | -    | -    | ٧    |
| , , ==                       | breakdown voltage  | $I_D = 250 \mu\text{A};  V_{GS} = 0  V;  T_j = -55 ^{\circ}\text{C}$                                      | 22.5 | -    | -    | V    |
| $V_{GS(th)}$                 | gate-source threshold voltage                            | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$  | 1.45 | 1.74 | 2.15 | V    |
| $\Delta V_{GS(th)}/\Delta T$ | gate-source threshold voltage variation with temperature |   | -    | -4.2 | -    | mV/K |
| I <sub>DSS</sub>             | drain leakage current                                    | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$  | -    | -    | 1    | μΑ   |
|                              |  | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$                                       | -    | -    | 100  | μΑ   |
| I <sub>GSS</sub>             | gate leakage current                                     | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$  | -    | -    | 100  | nA   |
|                              |  | $V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                       | -    | -    | 100  | nA   |
| $R_{DSon}$                   | drain-source on-state resistance                         | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$<br>see <u>Figure 10</u>                | -    | 3.25 | 3.75 | mΩ   |
|                              |  | $V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>               | -    | -    | 6    | mΩ   |
|                              |  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$<br>see <u>Figure 10</u>                 | -    | 2.45 | 2.8  | mΩ   |
|                              |  | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 150 °C;<br>see <u>Figure 10</u> ; see <u>Figure 11</u>             | -    | -    | 4.5  | mΩ   |
| $R_G$                        | gate resistance  | f = 1 MHz   | 0.37 | 0.74 | 1.48 | Ω    |
| Dynamic cha                  | aracteristics  |   |      |      |      |      |
| Q <sub>G(tot)</sub>          | total gate charge  | $I_D = 25 \text{ A}$ ; $V_{DS} = 12.5 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 12; see Figure 13 | -    | 37.7 | -    | nC   |
|                              |  | $I_D$ = 25 A; $V_{DS}$ = 12.5 V; $V_{GS}$ = 4.5 V;<br>see <u>Figure 12</u> ; see <u>Figure 13</u>         | -    | 16.3 | -    | nC   |
|                              |  | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$  | -    | 36.7 | -    | nC   |
| Q <sub>GS</sub>              | gate-source charge                                       | $I_D = 25 \text{ A}; V_{DS} = 12.5 \text{ V}; V_{GS} = 4.5 \text{ V};$                                    | -    | 6.5  | -    | nC   |
| Q <sub>GS(th)</sub>          | pre-threshold<br>gate-source charge                      | see Figure 12; see Figure 13  | -    | 3.9  | -    | nC   |
| Q <sub>GS(th-pl)</sub>       | post-threshold<br>gate-source charge                     |   | -    | 2.6  | -    | nC   |
| Q <sub>GD</sub>              | gate-drain charge  |   | -    | 3.9  | -    | nC   |
| $V_{GS(pl)}$                 | gate-source plateau<br>voltage                           | $I_D$ = 25 A; $V_{DS}$ = 12.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u>                              | -    | 2.9  | -    | V    |
| C <sub>iss</sub>             | input capacitance  | $V_{DS} = 12.5 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$                                       | -    | 2432 | -    | pF   |
| C <sub>oss</sub>             | output capacitance                                       | T <sub>j</sub> = 25 °C; see <u>Figure 14</u>  | -    | 533  | -    | pF   |
| $C_{rss}$                    | reverse transfer capacitance                             |   | -    | 198  | -    | pF   |

Table 6. Characteristics ... continued

| Symbol              | Parameter                  | Conditions   | Min | Тур  | Max | Unit |
|---------------------|----------------------------|--|-----|------|-----|------|
| $t_{d(on)}$         | turn-on delay time         | $V_{DS} = 12.5 \text{ V}; \ R_L = 0.5 \ \Omega; \ V_{GS} = 4.5 \text{ V}; \\ R_{G(ext)} = 5 \ \Omega$  | -   | 16.4 | -   | ns   |
| t <sub>r</sub>      | rise time                  |  | -   | 24.6 | -   | ns   |
| t <sub>d(off)</sub> | turn-off delay time        |  | -   | 19.9 | -   | ns   |
| t <sub>f</sub>      | fall time                  |  | -   | 13.1 | -   | ns   |
| Q <sub>oss</sub>    | output charge              | $V_{GS} = 0 \text{ V}; V_{DS} = 12.5 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ °C}$   | -   | 14.3 | -   | nC   |
| Source-drain        | n diode                    |  |     |      |     |      |
| $V_{SD}$            | source-drain voltage       | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$<br>see Figure 15  | -   | 0.82 | 1.1 | V    |
| t <sub>rr</sub>     | reverse recovery time      | $I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$  | -   | 21.3 | -   | ns   |
| Q <sub>r</sub>      | recovered charge           | V <sub>DS</sub> = 12.5 V   | -   | 14.1 | -   | nC   |
| ta                  | reverse recovery rise time | $V_{GS} = 0 \text{ V}; I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$<br>$V_{DS} = 12.5 \text{ V}; \text{see } \frac{\text{Figure } 16}{\text{Model}}$ | -   | 12.1 | -   | ns   |
| t <sub>b</sub>      | reverse recovery fall time |  | -   | 9.2  | -   | ns   |

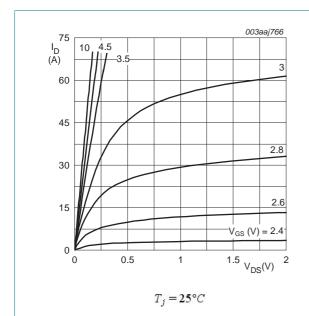


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

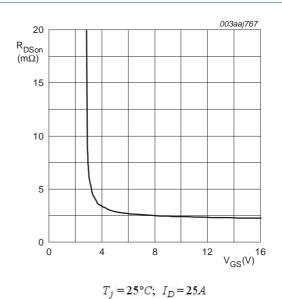


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

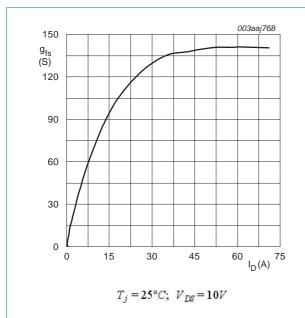


Fig 8. Forward transconductance as a function of drain current; typical values

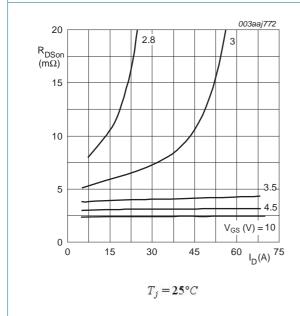


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

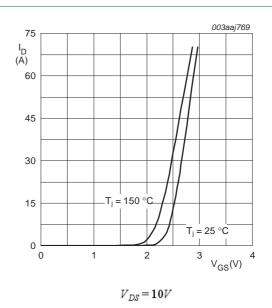


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

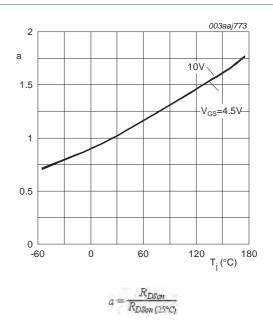


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

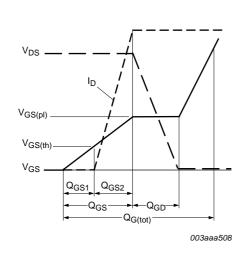


Fig 12. Gate charge waveform definitions

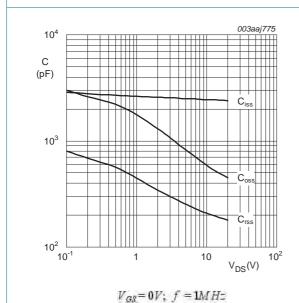
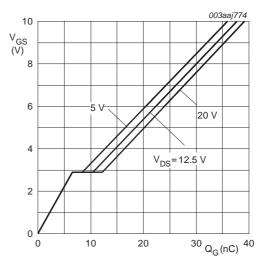


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 13. Gate-source voltage as a function of gate charge; typical values

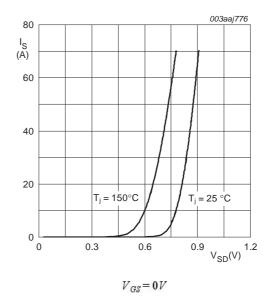
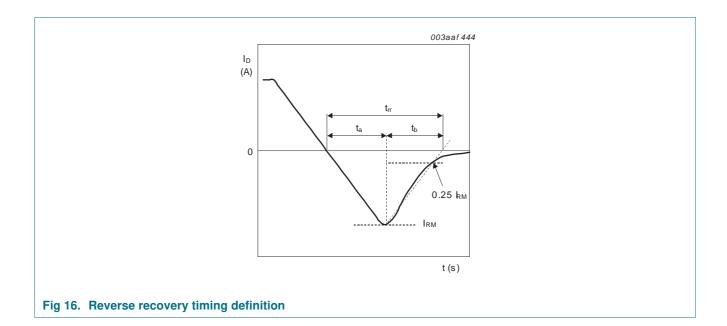


Fig 15. Source current as a function of source-drain voltage; typical values



### 7. Package outline

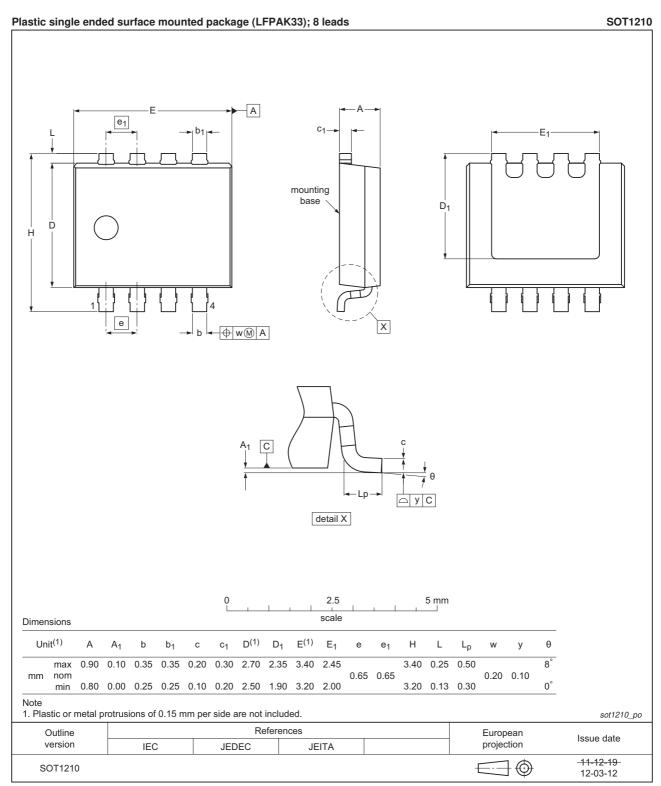


Fig 17. Package outline SOT1210 (LFPAK33)

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# 8. Revision history

#### Table 7. Revision history

| Document ID       | Release date                           | Data sheet status  | Change notice | Supersedes        |
|-------------------|--|--------------------|---------------|-------------------|
| PSMN2R8-25MLC v.3 | 20120615                               | Product data sheet | -             | PSMN2R8-25MLC v.2 |
| Modifications:    | <ul> <li>Various changes to</li> </ul> | content.           |               |                   |
| PSMN2R8-25MLC v.2 | 20120607                               | Product data sheet | -             | PSMN2R8-25MLC v.1 |

#### N-channel 25 V 2.8 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

### 9. Legal information

#### 9.1 Data sheet status

| Document status[1] [2]         | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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### 11. Contents

| 1   | Product profile         |
|-----|-------------------------|
| 1.1 | General description1    |
| 1.2 | Features and benefits   |
| 1.3 | Applications1           |
| 1.4 | Quick reference data    |
| 2   | Pinning information     |
| 3   | Ordering information    |
| 4   | Limiting values         |
| 5   | Thermal characteristics |
| 6   | Characteristics         |
| 7   | Package outline10       |
| 8   | Revision history11      |
| 9   | Legal information12     |
| 9.1 | Data sheet status       |
| 9.2 | Definitions12           |
| 9.3 | Disclaimers             |
| 9.4 | Trademarks13            |
| 10  | Contact information 13  |